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Correction: High throughput first-principles calculations of bixbyite oxides for TCO applications

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Correction for 'High throughput first-principles calculations of bixbyite oxides for TCO applications' by Nasrin Sarmadian *et al.*, *Phys. Chem. Chem. Phys.*, 2014, **16**, 17724–17733.

In all our calculations with the hybrid functional HSE06 the default value of 0.25 for the amount of exact exchange was adjusted to 0.325 in order to reproduce the experimentally available fundamental band gap of In₂O₃.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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